IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

the Application of: HAYASHI, et al.

Group Art Unit: 2813

Serial No.: 09/955,600

Examiner: Tuan H. Nguyen

Filed: September 19, 2001

Confirmation No.: 1668

SEMICONDUCTOR DEVICE AND METHOD OF FABRICATING

THE SAME AND METHOD OF FORMING NITRIDE BASED

SEMICONDUCTOR LAYER

Attorney Docket Number: 990852A

Customer Number: 38834

AMENDMENT AFTER FINAL REJECTION

BOX: AF Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

September 3, 2004

Sir:

In response to the Office Action dated March 5, 2004, please amend the above-identified application as follows:

Amendment to the Claims begins on page 2 of this paper.

Remarks begin on page 4 of this paper.